

NX3V1G384

Low-ohmic single-pole single-throw analog switch

Rev. 6 — 4 November 2011

Product data sheet

1. General description

The NX3V1G384 is a low-ohmic single-pole single-throw analog switch. It has two input/output terminals (Y and Z) and an active LOW enable input pin ($\bar{E}$). When pin $\bar{E}$ is HIGH, the analog switch is turned off.

Schmitt trigger action at the enable input ($\bar{E}$) makes the circuit tolerant to slower input rise and fall times. The NX3V1G384 allows signals with amplitude up to V_{CC} to be transmitted from Y to Z or from Z to Y. Its ultra-low ON resistance ($0.3\ \Omega$) and flatness ($0.1\ \Omega$) ensures minimal attenuation and distortion of transmitted signals.

2. Features and benefits

- Wide supply voltage range from 1.4 V to 4.3 V
- Very low ON resistance (peak):
 - ◆ $0.8\ \Omega$ (typical) at $V_{CC} = 1.4\text{ V}$
 - ◆ $0.5\ \Omega$ (typical) at $V_{CC} = 1.65\text{ V}$
 - ◆ $0.3\ \Omega$ (typical) at $V_{CC} = 2.3\text{ V}$
 - ◆ $0.25\ \Omega$ (typical) at $V_{CC} = 2.7\text{ V}$
 - ◆ $0.25\ \Omega$ (typical) at $V_{CC} = 4.3\text{ V}$
- High noise immunity
- ESD protection:
 - ◆ HBM JESD22-A114F Class 3A exceeds 7500 V
 - ◆ MM JESD22-A115-A exceeds 200 V
 - ◆ CDM AEC-Q100-011 revision B exceeds 1000 V
 - ◆ IEC61000-4-2 contact discharge exceeds 6000 V for switch ports
- CMOS low-power consumption
- Latch-up performance exceeds 100 mA per JESD 78B Class II Level A
- Direct interface with TTL levels at 3.0 V
- Control input accepts voltages above supply voltage
- High current handling capability (500 mA continuous current under 3.3 V supply)
- Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$

3. Applications

- Cell phone
- PDA
- Portable media player



4. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
NX3V1G384GW	−40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1
NX3V1G384GM	−40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1.45 × 0.5 mm	SOT886

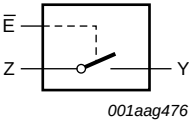
5. Marking

Table 2. Marking codes^[1]

Type number	Marking code
NX3V1G384GW	eL
NX3V1G384GM	eL

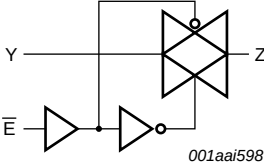
[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

6. Functional diagram



001aag476

Fig 1. Logic symbol

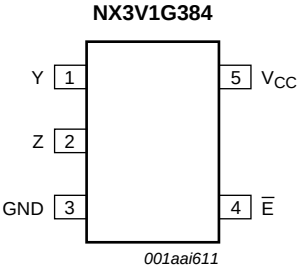


001aai598

Fig 2. Logic diagram

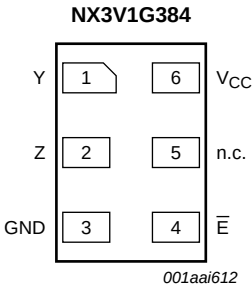
7. Pinning information

7.1 Pinning



001aai611

Fig 3. Pin configuration SOT353-1 (TSSOP5)



001aai612

Transparent top view

Fig 4. Pin configuration SOT886 (XSON6)

7.2 Pin description

Table 3. Pin description

Symbol	Pin		Description
	SOT353-1	SOT886	
Y	1	1	independent input or output
Z	2	2	independent output or input
GND	3	3	ground (0 V)
$\overline{E}$	4	4	enable input (active LOW)
n.c.	-	5	not connected
V _{CC}	5	6	supply voltage

8. Functional description

Table 4. Function table^[1]

Input $\overline{E}$	Switch
L	ON
H	OFF

[1] H = HIGH voltage level; L = LOW voltage level.

9. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+4.6	V
V _I	input voltage	enable input $\overline{E}$	^[1] -0.5	+4.6	V
V _{SW}	switch voltage		^[2] -0.5	V _{CC} + 0.5	V
I _{IK}	input clamping current	V _I < -0.5 V	-50	-	mA
I _{SK}	switch clamping current	V _I < -0.5 V or V _I > V _{CC} + 0.5 V	-	±50	mA
I _{SW}	switch current	V _{SW} > -0.5 V or V _{SW} < V _{CC} + 0.5 V; source or sink current	-	±500	mA
		V _{SW} > -0.5 V or V _{SW} < V _{CC} + 0.5 V; pulsed at 1 ms duration, < 10 % duty cycle; peak current	-	±750	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	T _{amb} = -40 °C to +125 °C	^[3] -	250	mW

[1] The minimum input voltage rating may be exceeded if the input current rating is observed.

[2] The minimum and maximum switch voltage ratings may be exceeded if the switch clamping current rating is observed but may not exceed 4.6 V.

[3] For TSSOP5 package: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K.
For XSON6 package: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

10. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CC}	supply voltage		1.4	-	4.3	V
V_I	input voltage	enable input $\bar{E}$	0	-	4.3	V
V_{SW}	switch voltage		[1] 0	-	V_{CC}	V
T_{amb}	ambient temperature		-40	-	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 1.4\text{ V to }3.6\text{ V}$	[2] -	-	200	ns/V

[1] To avoid sinking GND current from of terminal Z when switch current flows in terminal Y, the voltage drop across the bidirectional switch must not exceed 0.4 V. If the switch current flows into terminal Z, no GND current will flow from terminal Y. In this case, there is no limit for the voltage drop across the switch.

[2] Applies to control signal levels.

11. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground 0 V).

Symbol	Parameter	Conditions	$T_{amb} = 25\text{ °C}$			$T_{amb} = -40\text{ °C to }+125\text{ °C}$			Unit
			Min	Typ	Max	Min	Max (85 °C)	Max (125 °C)	
V_{IH}	HIGH-level input voltage	$V_{CC} = 1.4\text{ V to }1.95\text{ V}$	$0.65V_{CC}$	-	-	$0.65V_{CC}$	-	-	V
		$V_{CC} = 2.3\text{ V to }2.7\text{ V}$	1.7	-	-	1.7	-	-	V
		$V_{CC} = 2.7\text{ V to }3.6\text{ V}$	2.0	-	-	2.0	-	-	V
		$V_{CC} = 3.6\text{ V to }4.3\text{ V}$	$0.7V_{CC}$	-	-	$0.7V_{CC}$	-	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 1.4\text{ V to }1.95\text{ V}$	-	-	$0.35V_{CC}$	-	$0.35V_{CC}$	$0.35V_{CC}$	V
		$V_{CC} = 2.3\text{ V to }2.7\text{ V}$	-	-	0.7	-	0.7	0.7	V
		$V_{CC} = 2.7\text{ V to }3.6\text{ V}$	-	-	0.8	-	0.8	0.8	V
		$V_{CC} = 3.6\text{ V to }4.3\text{ V}$	-	-	$0.3V_{CC}$	-	$0.3V_{CC}$	$0.3V_{CC}$	V
I_I	input leakage current	enable input $\bar{E}$; $V_I = \text{GND to }4.3\text{ V}$; $V_{CC} = 1.4\text{ V to }4.3\text{ V}$	-	-	-	-	± 0.5	± 1	μA
$I_{S(OFF)}$	OFF-state leakage current	Y port; see Figure 5 ;							
		$V_{CC} = 1.4\text{ V to }3.6\text{ V}$	-	-	± 5	-	± 50	± 500	nA
		$V_{CC} = 3.6\text{ V to }4.3\text{ V}$	-	-	± 10	-	± 50	± 500	nA
$I_{S(ON)}$	ON-state leakage current	Z port; see Figure 6 ;							
		$V_{CC} = 1.4\text{ V to }3.6\text{ V}$	-	-	± 5	-	± 50	± 500	nA
		$V_{CC} = 3.6\text{ V to }4.3\text{ V}$	-	-	± 10	-	± 50	± 500	nA
I_{CC}	supply current	$V_I = V_{CC}\text{ or GND}$; $V_{SW} = \text{GND or }V_{CC}$	-	-	± 100	-	690	6000	nA
		$V_{CC} = 3.6\text{ V}$	-	-	100	-	690	6000	nA
		$V_{CC} = 4.3\text{ V}$	-	-	150	-	800	7000	nA

Symbol	Parameter	Conditions	T _{amb} = 25 °C			T _{amb} = –40 °C to +125 °C			Unit
			Min	Typ	Max	Min	Max (85 °C)	Max (125 °C)	
C _I	input capacitance		-	1.0	-	-	-	-	pF
C _{S(OFF)}	OFF-state capacitance		-	70	-	-	-	-	pF
C _{S(ON)}	ON-state capacitance		-	205	-	-	-	-	pF

Figure 5 shows a test circuit for measuring OFF-state leakage current. A MOSFET is shown with its gate connected to V_{CC} and its source connected to GND. The drain is connected to a voltage source V_I and a current source I_S in parallel. The output voltage V_O is measured across the current source I_S . The input voltage V_{IH} is applied to the gate through a dashed line, indicating it is not connected to the circuit.

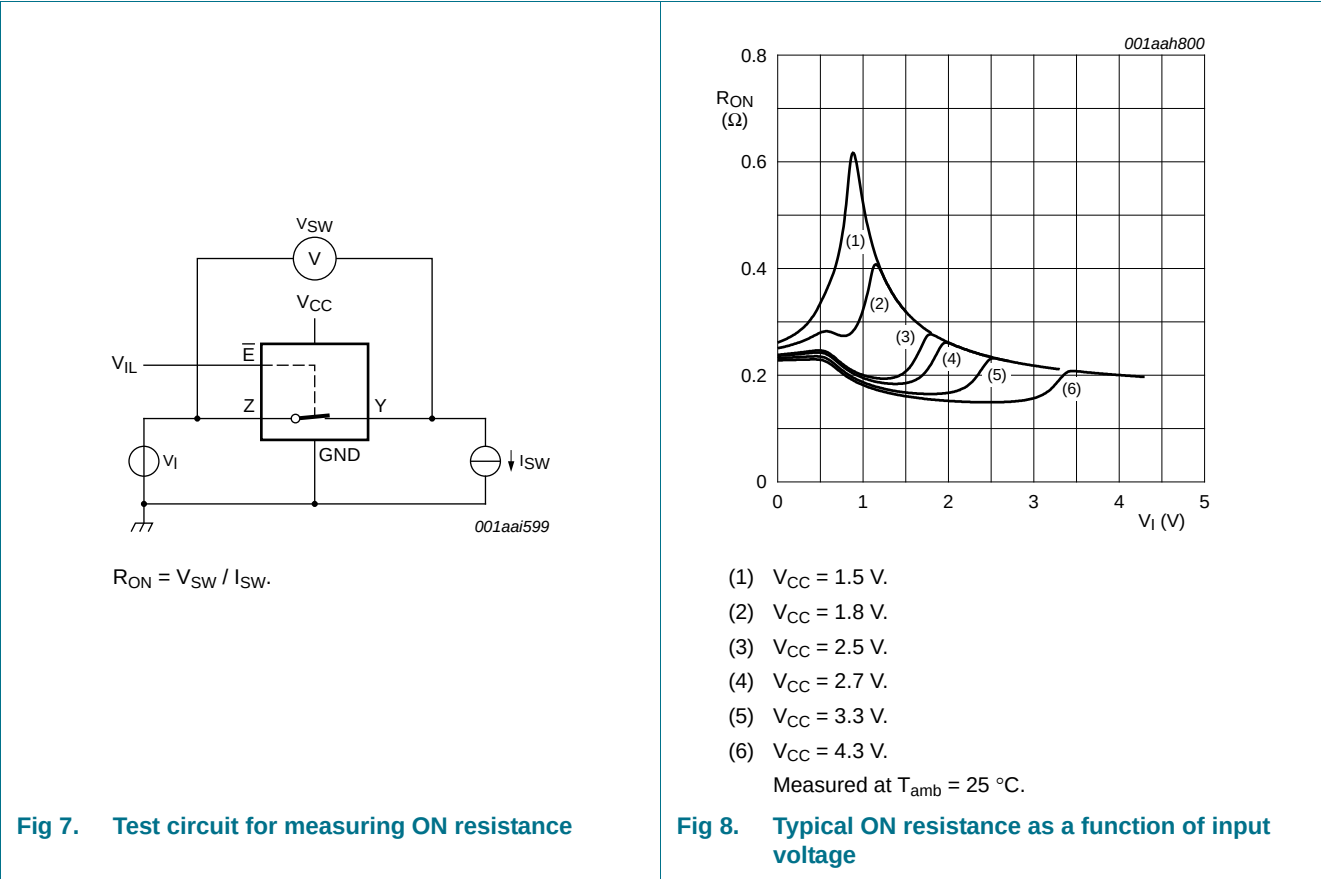
Figure 6 shows a test circuit for measuring ON-state leakage current. A MOSFET is shown with its gate connected to V_{CC} and its source connected to GND. The drain is connected to a voltage source V_I and a current source I_S in parallel. The output voltage V_O is measured across the current source I_S . The input voltage V_{IL} is applied to the gate through a dashed line, indicating it is not connected to the circuit.

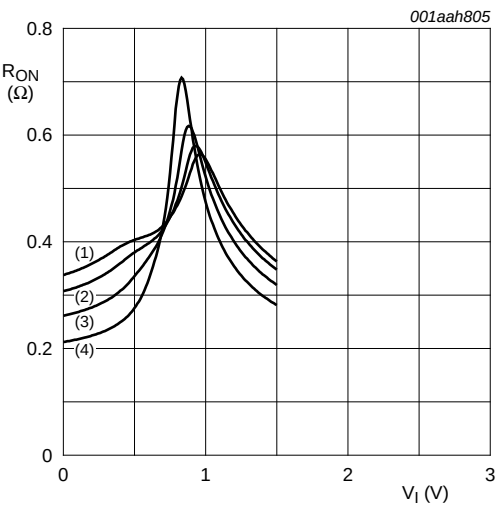
Table 8. Resistance R_{ON}

Symbol	Parameter	Conditions	T _{amb} = -40 °C to +85 °C			T _{amb} = -40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
R _{ON(peak)}	ON resistance (peak)	V _I = GND to V _{CC} ; I _{SW} = 100 mA; see Figure 7						
		V _{CC} = 1.4 V	-	0.8	1.9	-	2.1	Ω
		V _{CC} = 1.65 V	-	0.5	0.8	-	0.9	Ω
		V _{CC} = 2.3 V	-	0.3	0.5	-	0.6	Ω
		V _{CC} = 2.7 V	-	0.25	0.45	-	0.5	Ω
		V _{CC} = 4.3 V	-	0.25	0.45	-	0.5	Ω
R _{ON(flat)}	ON resistance (flatness)	V _I = GND to V _{CC} ; I _{SW} = 100 mA						
		V _{CC} = 1.4 V	-	0.5	1.7	-	1.8	Ω
		V _{CC} = 1.65 V	-	0.25	0.6	-	0.7	Ω
		V _{CC} = 2.3 V	-	0.1	0.2	-	0.2	Ω
		V _{CC} = 2.7 V	-	0.1	0.2	-	0.2	Ω
		V _{CC} = 4.3 V	-	0.1	0.25	-	0.25	Ω

- [1] Typical values are measured at $T_{amb} = 25\text{ }^{\circ}\text{C}$.
- [2] Flatness is defined as the difference between the maximum and minimum value of ON resistance measured at identical V_{CC} and temperature.

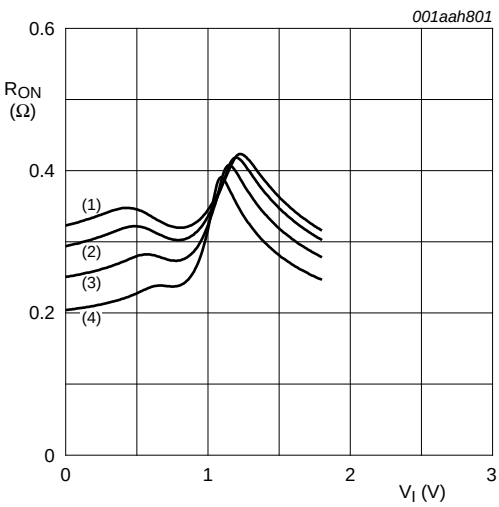
11.3 ON resistance test circuit and graphs





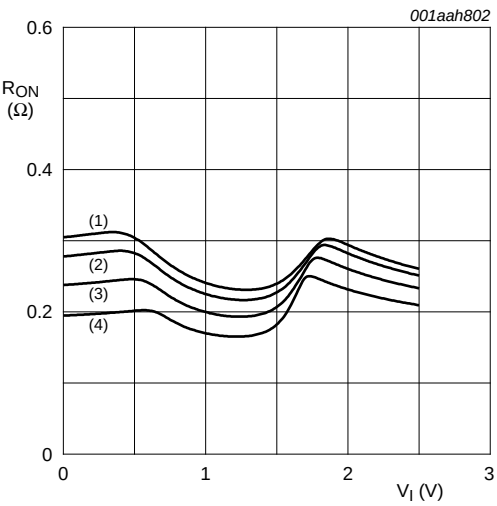
- (1) $T_{amb} = 125\text{ }^{\circ}\text{C}.$
- (2) $T_{amb} = 85\text{ }^{\circ}\text{C}.$
- (3) $T_{amb} = 25\text{ }^{\circ}\text{C}.$
- (4) $T_{amb} = -40\text{ }^{\circ}\text{C}.$

Fig 9. ON resistance as a function of input voltage;
 $V_{CC} = 1.5\text{ V}$



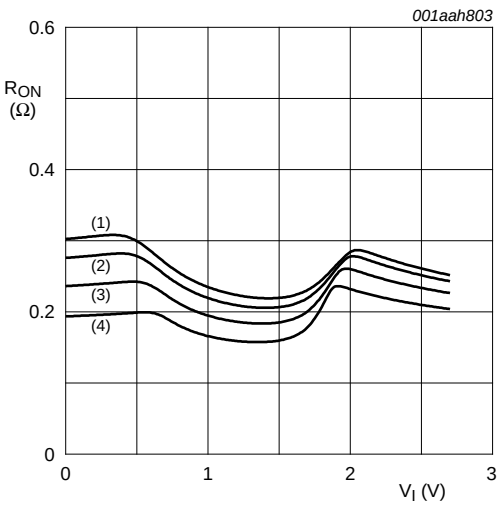
- (1) $T_{amb} = 125\text{ }^{\circ}\text{C}.$
- (2) $T_{amb} = 85\text{ }^{\circ}\text{C}.$
- (3) $T_{amb} = 25\text{ }^{\circ}\text{C}.$
- (4) $T_{amb} = -40\text{ }^{\circ}\text{C}.$

Fig 10. ON resistance as a function of input voltage;
 $V_{CC} = 1.8\text{ V}$



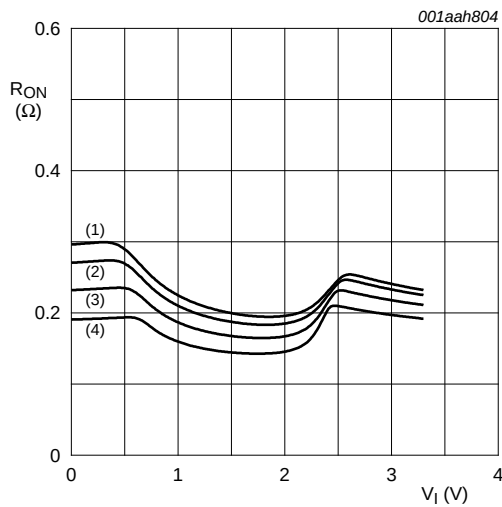
- (1) $T_{amb} = 125\text{ }^{\circ}\text{C}.$
- (2) $T_{amb} = 85\text{ }^{\circ}\text{C}.$
- (3) $T_{amb} = 25\text{ }^{\circ}\text{C}.$
- (4) $T_{amb} = -40\text{ }^{\circ}\text{C}.$

Fig 11. ON resistance as a function of input voltage;
 $V_{CC} = 2.5\text{ V}$



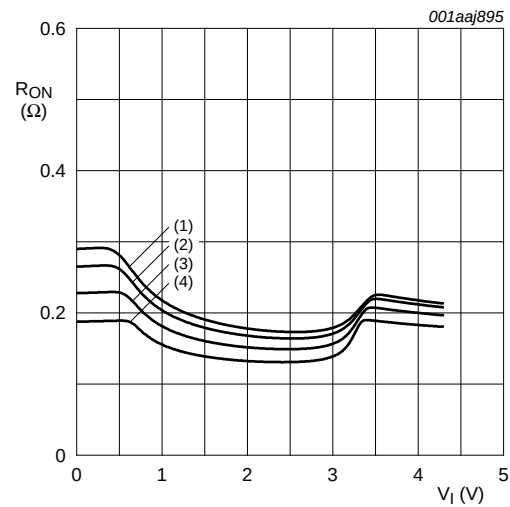
- (1) $T_{amb} = 125\text{ }^{\circ}\text{C}.$
- (2) $T_{amb} = 85\text{ }^{\circ}\text{C}.$
- (3) $T_{amb} = 25\text{ }^{\circ}\text{C}.$
- (4) $T_{amb} = -40\text{ }^{\circ}\text{C}.$

Fig 12. ON resistance as a function of input voltage;
 $V_{CC} = 2.7\text{ V}$



- (1) $T_{amb} = 125\text{ }^{\circ}\text{C}$.
- (2) $T_{amb} = 85\text{ }^{\circ}\text{C}$.
- (3) $T_{amb} = 25\text{ }^{\circ}\text{C}$.
- (4) $T_{amb} = -40\text{ }^{\circ}\text{C}$.

Fig 13. ON resistance as a function of input voltage;
 $V_{CC} = 3.3\text{ V}$



- (1) $T_{amb} = 125\text{ }^{\circ}\text{C}$.
- (2) $T_{amb} = 85\text{ }^{\circ}\text{C}$.
- (3) $T_{amb} = 25\text{ }^{\circ}\text{C}$.
- (4) $T_{amb} = -40\text{ }^{\circ}\text{C}$.

Fig 14. ON resistance as a function of input voltage;
 $V_{CC} = 4.3\text{ V}$

12. Dynamic characteristics

Table 9. Dynamic characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); for load circuit [Figure 16](#).

Symbol	Parameter	Conditions	$T_{amb} = 25\text{ }^{\circ}\text{C}$			$T_{amb} = -40\text{ }^{\circ}\text{C to } +125\text{ }^{\circ}\text{C}$			Unit
			Min	Typ ^[1]	Max	Min	Max (85 °C)	Max (125 °C)	
t_{en}	enable time	$\bar{E}$ to Z or Y; see Figure 15							
		$V_{CC} = 1.4\text{ V to } 1.6\text{ V}$	-	28	43	-	46	50	ns
		$V_{CC} = 1.65\text{ V to } 1.95\text{ V}$	-	23	36	-	39	43	ns
		$V_{CC} = 2.3\text{ V to } 2.7\text{ V}$	-	18	28	-	30	32	ns
		$V_{CC} = 2.7\text{ V to } 3.6\text{ V}$	-	15	26	-	27	29	ns
		$V_{CC} = 3.6\text{ V to } 4.3\text{ V}$	-	15	26	-	27	29	ns
t_{dis}	disable time	$\bar{E}$ to Z or Y; see Figure 15							
		$V_{CC} = 1.4\text{ V to } 1.6\text{ V}$	-	12	23	-	24	26	ns
		$V_{CC} = 1.65\text{ V to } 1.95\text{ V}$	-	9	16	-	18	19	ns
		$V_{CC} = 2.3\text{ V to } 2.7\text{ V}$	-	6	11	-	12	13	ns
		$V_{CC} = 2.7\text{ V to } 3.6\text{ V}$	-	5	10	-	11	12	ns
		$V_{CC} = 3.6\text{ V to } 4.3\text{ V}$	-	5	10	-	11	12	ns

[1] Typical values are measured at $T_{amb} = 25\text{ }^{\circ}\text{C}$ and $V_{CC} = 1.5\text{ V, } 1.8\text{ V, } 2.5\text{ V, } 3.3\text{ V}$ and 4.3 V respectively.

12.1 Waveform and test circuits

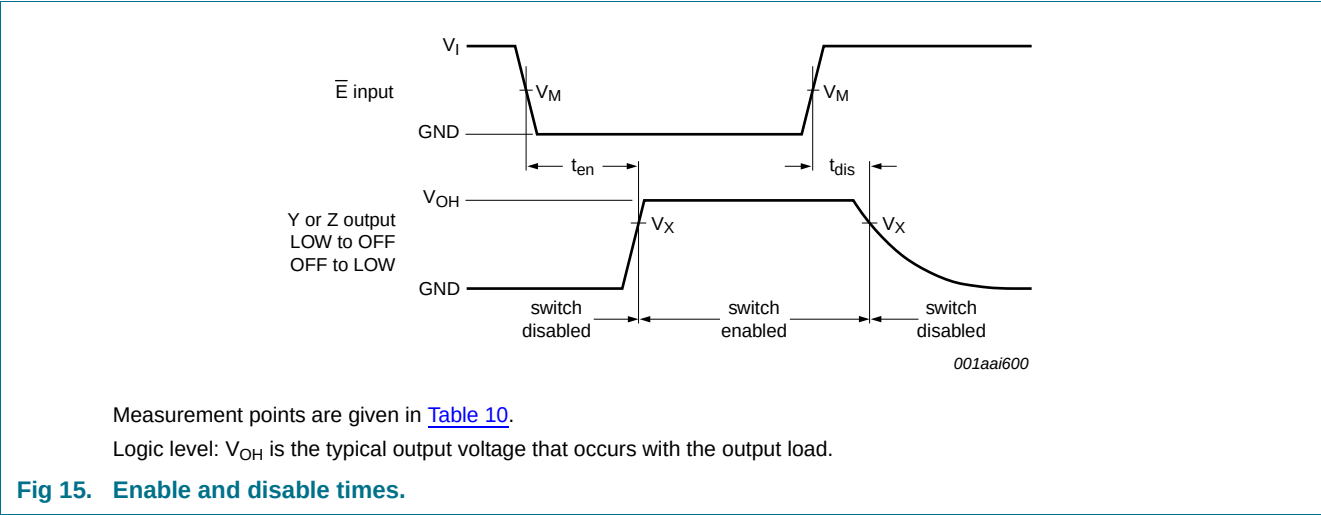


Table 10. Measurement points

Supply voltage	Input	Output
V_{CC}	V_M	V_X
1.4 V to 4.3 V	$0.5V_{CC}$	$0.9V_{OH}$

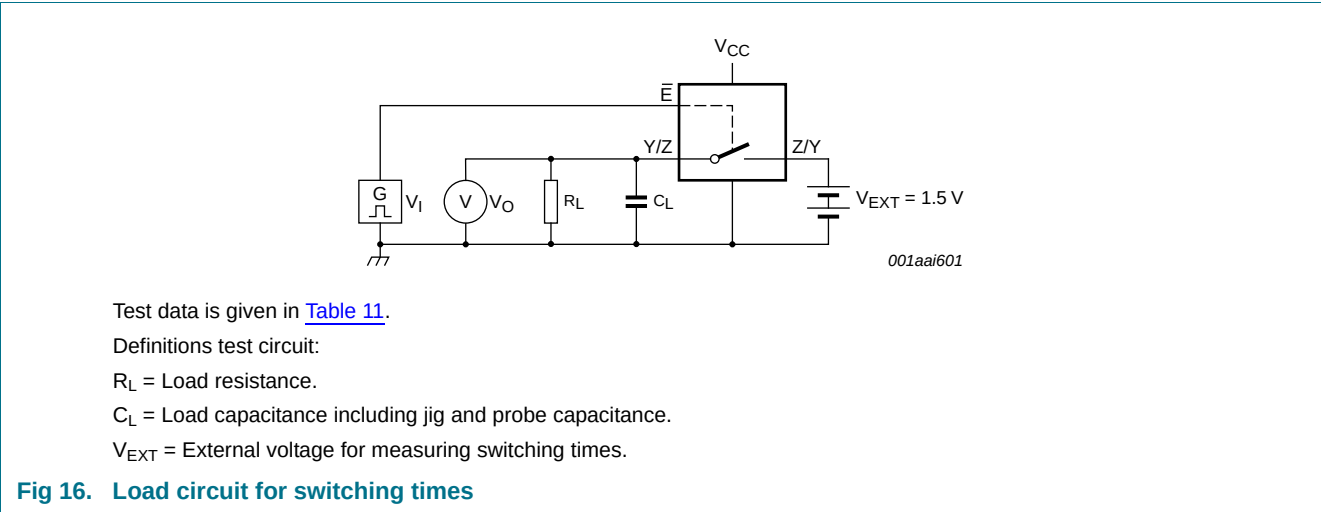


Table 11. Test data

Supply voltage	Input		Load	
V_{CC}	V_I	t_r, t_f	C_L	R_L
1.4 V to 4.3 V	V_{CC}	$\leq 2.5\text{ ns}$	35 pF	50 Ω

12.2 Additional dynamic characteristics

Table 12. Additional dynamic characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); $V_I = \text{GND}$ or V_{CC} (unless otherwise specified); $t_r = t_f \leq 2.5 \text{ ns}$.

Symbol	Parameter	Conditions	$T_{\text{amb}} = 25 \text{ }^{\circ}\text{C}$			Unit
			Min	Typ	Max	
THD	total harmonic distortion	$f_i = 20 \text{ Hz to } 20 \text{ kHz}$; $R_L = 32 \text{ } \Omega$; see Figure 17 [1]				
		$V_{CC} = 1.4 \text{ V}$; $V_I = 1 \text{ V (p-p)}$	-	0.05	-	%
		$V_{CC} = 1.65 \text{ V}$; $V_I = 1.2 \text{ V (p-p)}$	-	0.03	-	%
		$V_{CC} = 2.3 \text{ V}$; $V_I = 1.5 \text{ V (p-p)}$	-	0.01	-	%
		$V_{CC} = 2.7 \text{ V}$; $V_I = 2 \text{ V (p-p)}$	-	0.01	-	%
		$V_{CC} = 4.3 \text{ V}$; $V_I = 2 \text{ V (p-p)}$	-	0.01	-	%
$f_{(-3\text{dB})}$	–3 dB frequency response	$R_L = 50 \text{ } \Omega$; see Figure 18 [1]				
		$V_{CC} = 1.4 \text{ V to } 4.3 \text{ V}$	-	25	-	MHz
α_{iso}	isolation (OFF-state)	$f_i = 100 \text{ kHz}$; $R_L = 50 \text{ } \Omega$; see Figure 19 [1]				
		$V_{CC} = 1.4 \text{ V to } 4.3 \text{ V}$	-	–90	-	dB
V_{ct}	crosstalk voltage	between digital inputs and switch; $f_i = 1 \text{ MHz}$; $C_L = 50 \text{ pF}$; $R_L = 50 \text{ } \Omega$; see Figure 20				
		$V_{CC} = 1.4 \text{ V to } 3.6 \text{ V}$	-	0.3	-	V
		$V_{CC} = 3.6 \text{ V to } 4.3 \text{ V}$	-	0.5	-	V
Q_{inj}	charge injection	$f_i = 1 \text{ MHz}$; $C_L = 0.1 \text{ nF}$; $R_L = 1 \text{ M}\Omega$; $V_{\text{gen}} = 0 \text{ V}$; $R_{\text{gen}} = 0 \text{ } \Omega$; see Figure 21				
		$V_{CC} = 1.5 \text{ V}$	-	6.5	-	pC
		$V_{CC} = 1.8 \text{ V}$	-	6.5	-	pC
		$V_{CC} = 2.5 \text{ V}$	-	6.5	-	pC
		$V_{CC} = 3.3 \text{ V}$	-	6.5	-	pC
		$V_{CC} = 4.3 \text{ V}$	-	12	-	pC

[1] f_i is biased at $0.5V_{CC}$.

12.3 Test circuits

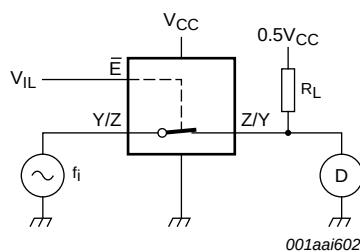
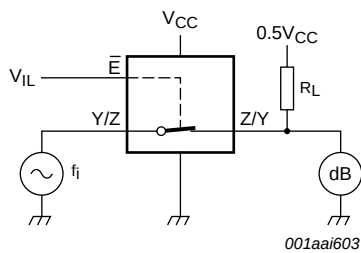
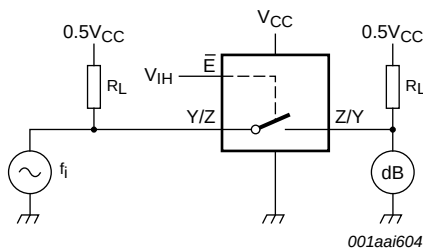


Fig 17. Test circuit for measuring total harmonic distortion



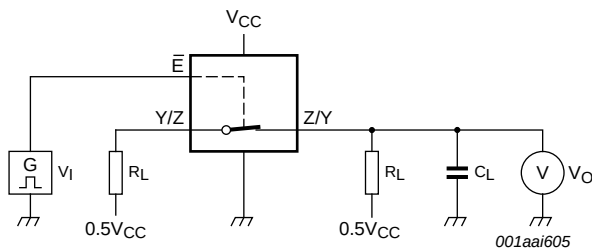
Adjust f_i voltage to obtain 0 dBm level at output. Increase f_i frequency until dB meter reads -3 dB.

Fig 18. Test circuit for measuring the frequency response when channel is in ON-state

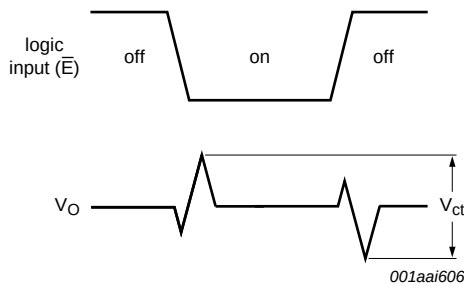


Adjust f_i voltage to obtain 0 dBm level at input.

Fig 19. Test circuit for measuring isolation (OFF-state)

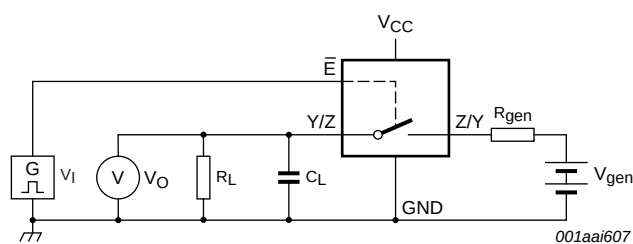


a. Test circuit

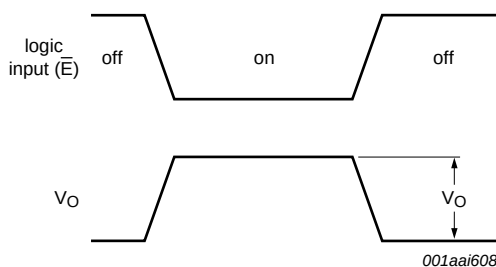


b. input and output pulse definitions

Fig 20. Test circuit for measuring crosstalk voltage between digital inputs and switch



a. Test circuit.



b. Input and output pulse definitions.

Definition: $Q_{inj} = \Delta V_O \times C_L$.

ΔV_O = output voltage variation.

R_{gen} = generator resistance.

V_{gen} = generator voltage.

Fig 21. Test circuit for measuring charge injection

13. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mmSOT353-1

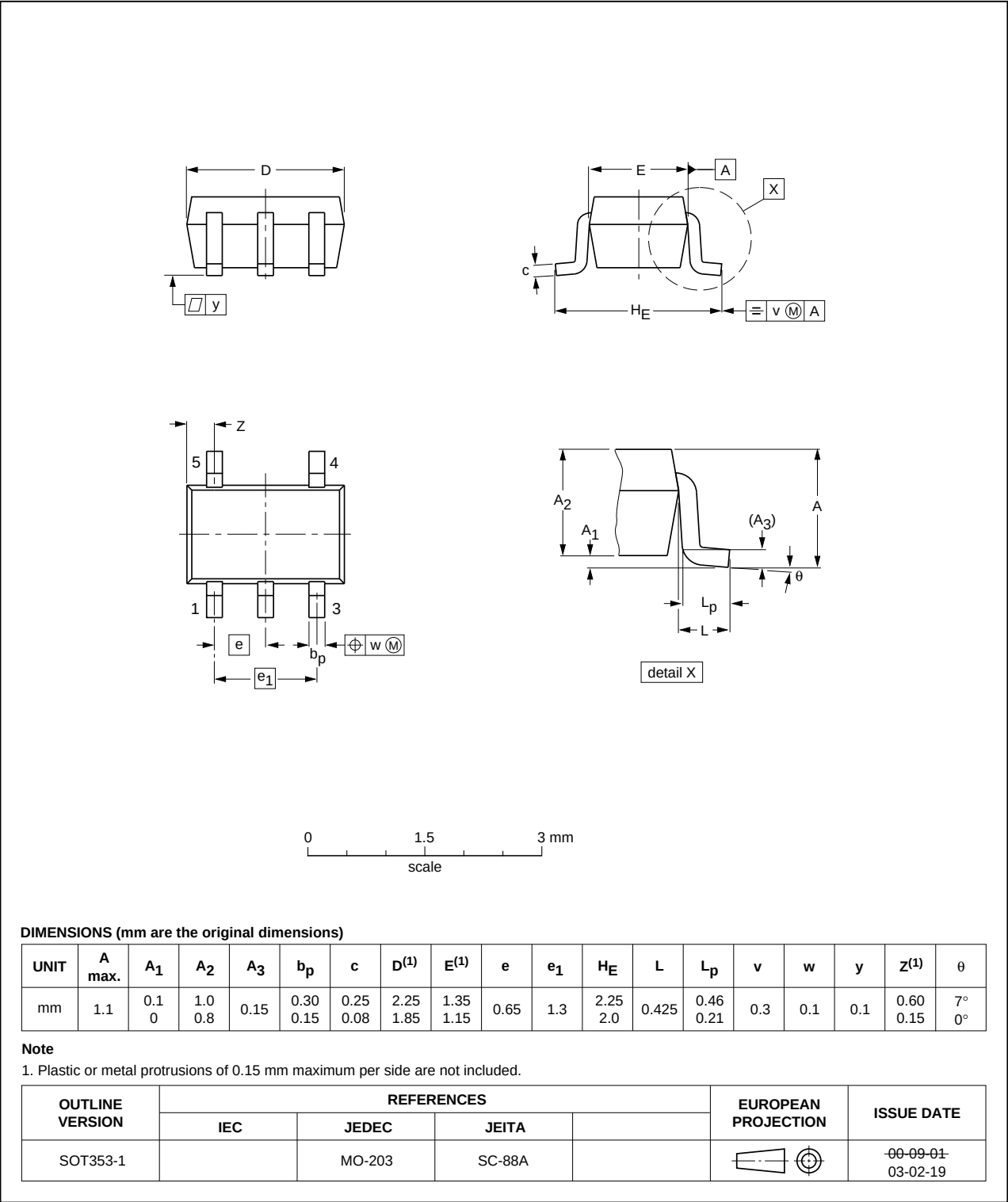


Fig 22. Package outline SOT353-1 (TSSOP5)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1.45 x 0.5 mm

SOT886

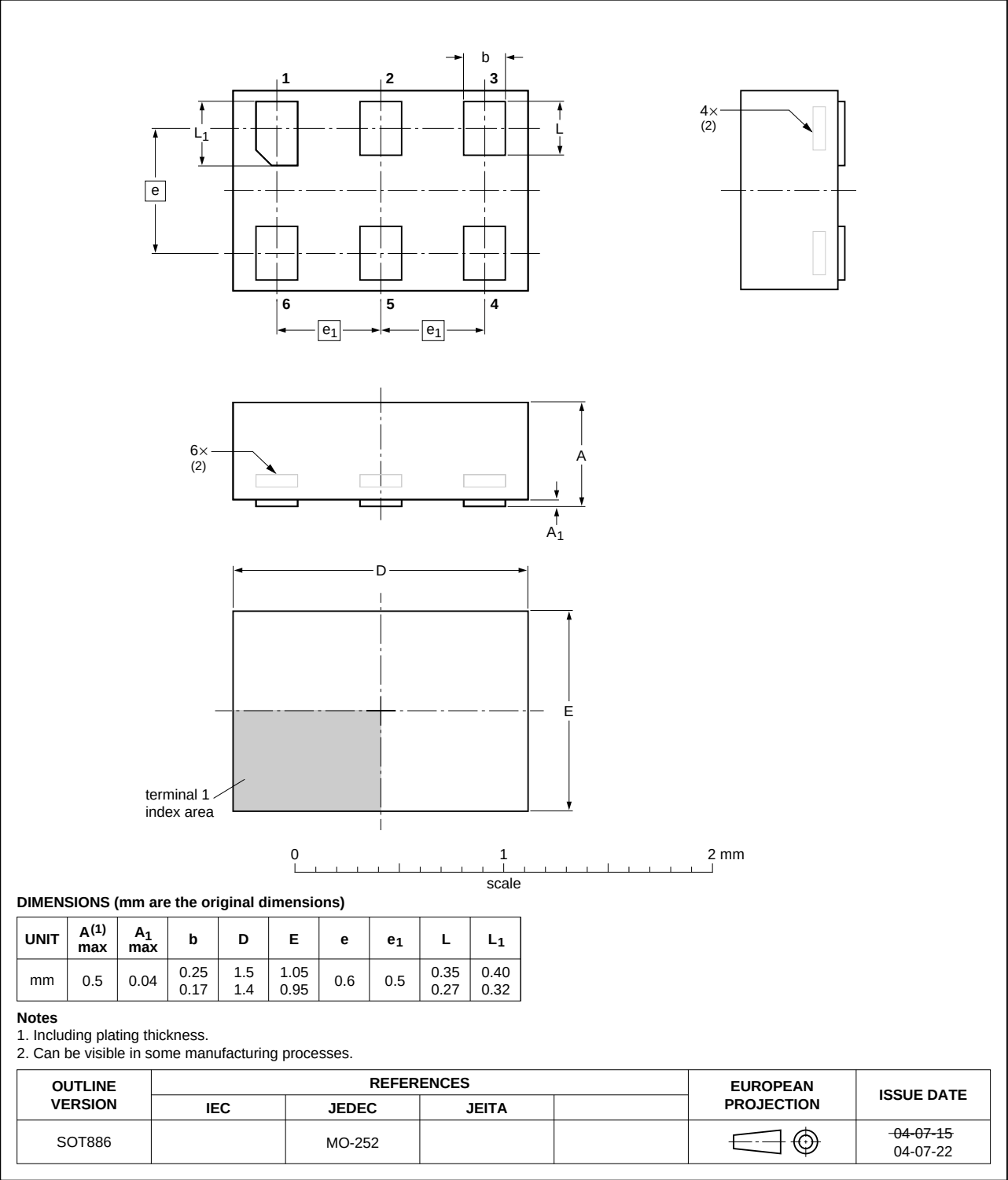


Fig 23. Package outline SOT886 (XSON6)

14. Abbreviations

Table 13. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal-Oxide Semiconductor
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
PDA	Personal Digital Assistant
TTL	Transistor-Transistor Logic

15. Revision history

Table 14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
NX3V1G384 v.6	20111104	Product data sheet	-	NX3V1G384 v.5
Modifications:	• Legal pages updated.			
NX3V1G384 v.5	20101220	Product data sheet	-	NX3V1G384 v.4
NX3V1G384 v.4	20100324	Product data sheet	-	NX3V1G384 v.3
NX3V1G384 v.3	20100208	Product data sheet	-	NX3V1G384 v.2
NX3V1G384 v.2	20090414	Product data sheet	-	NX3V1G384 v.1
NX3V1G384 v.1	20080918	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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